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Form PTO-1449	U.S. Department of Commerce Patent and Trademark Office	Attorney Docket No. 5347-208	Serial No. 09/891,552
LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)		Applicants: Gerald Lucovsky et al.	
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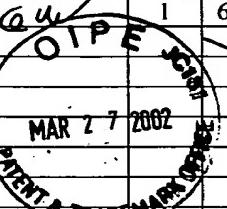
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<i>Aug</i>	6	International Search Report, PCT/US01/19787, February 15, 2002					
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